

Abstracts

High Power V-Band Double Drift IMPATT Amplifier

K.P. Weller, D.L. English and E.M. Nakaji. "High Power V-Band Double Drift IMPATT Amplifier." 1978 MTT-S International Microwave Symposium Digest 78.1 (1978 [MWSYM]): 369-371.

A 490 mW circulator-coupled IMPATT reflection amplifier with 6.9 dB gain at 59.25 GHz and 1.9 GHz bandwidth for 1 dB rolloff has been developed using double-drift IMPATT diodes on diamond in a novel circuit designed to minimize subharmonic instabilities.

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